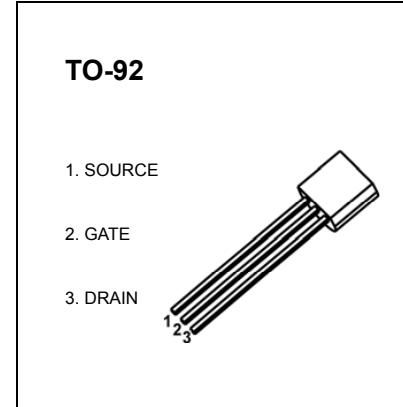


## <A7000

MOSFET (N-Channel)

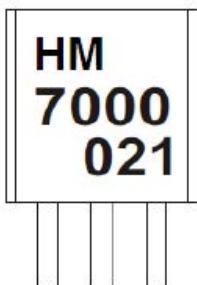
$V_{(BR)DSS}$	$R_{DS(on)}\text{MAX}$	$I_D$
60 V	5Ω@10V	200mA
	6Ω@4.5V	



### FEATURE

- High density cell design for low  $R_{DS(\text{ON})}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

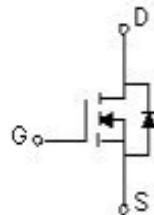
### MARKING



### APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

### Equivalent Circuit



### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Continuous Drain Current	$I_D$	0.2	A
Power Dissipation	$P_D$	0.625	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	200	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55 ~+150	

## MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$  unless otherwise specified

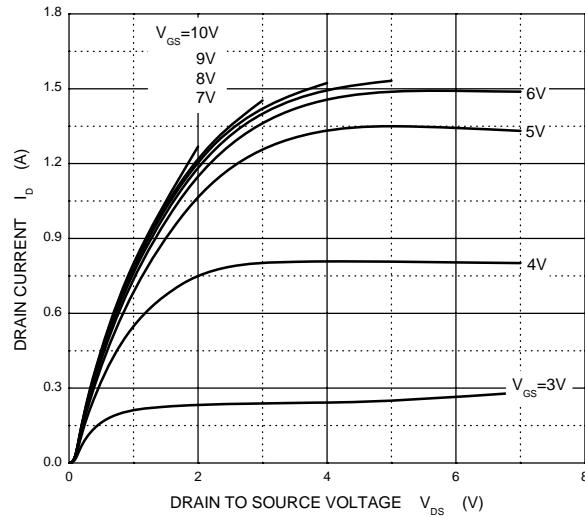
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
<b>Drain-Source Breakdown Voltage</b>	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{ V}, I_D=10\mu\text{A}$	60			V
<b>Gate-Threshold Voltage*</b>	$V_{(\text{GS})\text{th}}$	$V_{\text{DS}}=V_{\text{GS}}, I_D=1\text{mA}$	0.8		3	
<b>Gate-body Leakage</b>	$I_{\text{GSS}}$	$V_{\text{DS}}=0\text{ V}, V_{\text{GS}}=\pm 15\text{ V}$			$\pm 10$	nA
<b>Zero Gate Voltage Drain Current</b>	$I_{\text{DSS}}$	$V_{\text{DS}}=60\text{ V}, V_{\text{GS}}=0\text{ V}$			1	$\mu\text{A}$
<b>On-state Drain Current</b>	$I_{\text{D}(\text{ON})}$	$V_{\text{GS}}=4.5\text{ V}, V_{\text{DS}}=10\text{ V}$	75			mA
<b>Drain-Source On-Resistance*</b>	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=4.5\text{V}, I_D=75\text{mA}$			6	$\Omega$
		$V_{\text{GS}}=10\text{V}, I_D=500\text{mA}$			5	
<b>Forward Trans conductance*</b>	$g_{\text{fs}}$	$V_{\text{DS}}=10\text{ V}, I_D=200\text{mA}$	100			ms
<b>Drain-source on-voltage*</b>	$V_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10\text{V}, I_D=500\text{mA}$			2.5	V
		$V_{\text{GS}}=4.5\text{V}, I_D=75\text{mA}$			0.45	V
<b>Input Capacitance **</b>	$C_{\text{iss}}$	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$			60	pF
<b>Output Capacitance **</b>	$C_{\text{oss}}$				25	
<b>Reverse Transfer Capacitance **</b>	$C_{\text{rss}}$				5	
<b>Turn-on Time **</b>	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=15\text{ V}, R_L=30\Omega$ $I_D=500\text{mA}, V_{\text{GEN}}=10\text{ V}$ $R_G=25\Omega$			10	ns
<b>Turn-off Time **</b>	$t_{\text{d}(\text{off})}$				10	

\*Pulse test

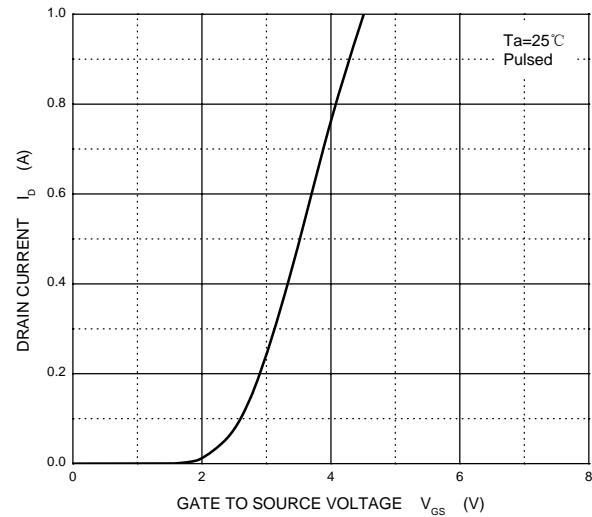
\*\*These parameters have no way to verify.

## Typical Characteristics

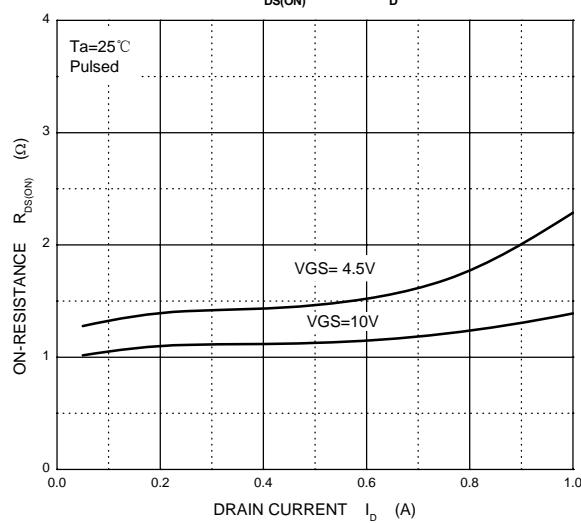
**Output Characteristics**



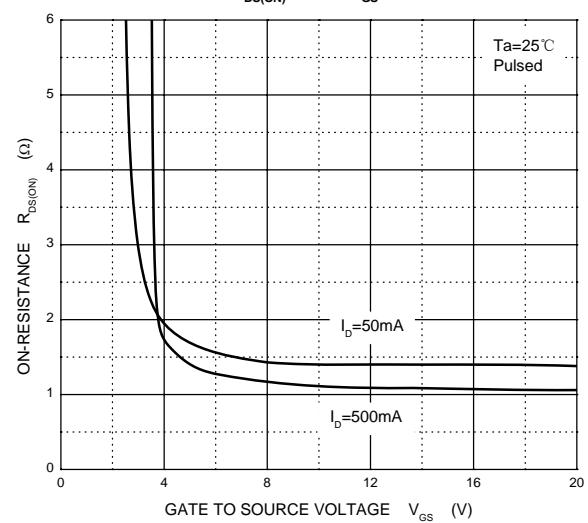
**Transfer Characteristics**



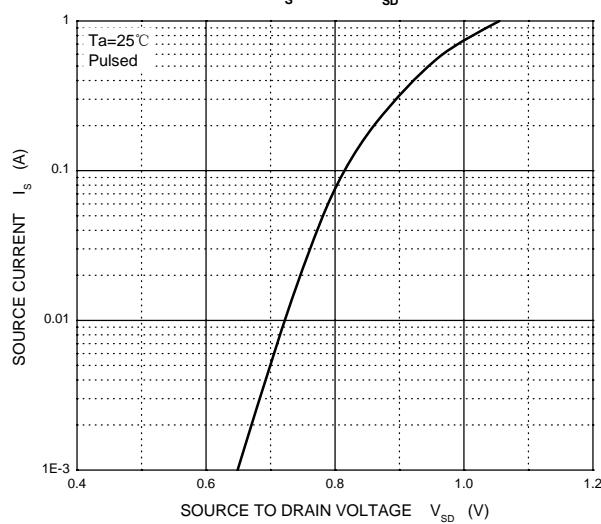
$R_{DS(ON)}$  —  $I_D$



$R_{DS(ON)}$  —  $V_{GS}$



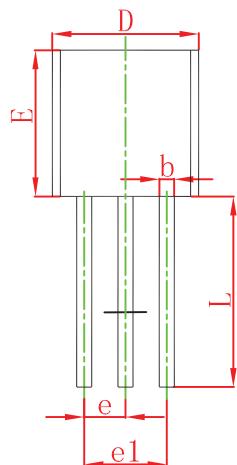
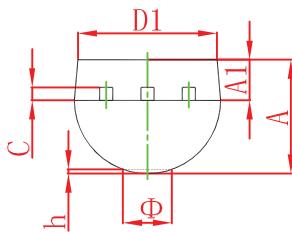
$I_S$  —  $V_{SD}$



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## TO-92 Package Outline Dimensions

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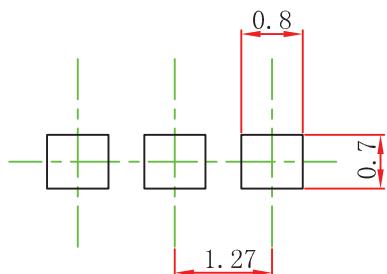


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	3.400	3.600	0.134	0.142
A1	1.150	1.350	0.045	0.053
b	0.380	0.550	0.015	0.022
c	0.410	0.510	0.016	0.020
D	4.400	4.600	0.173	0.181
D1	3.430		0.135	
E	4.400	4.600	0.173	0.181
e	1.270 TYP.		0.050 TYP.	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ	1.600		0.063	
h	0.000	0.380	0.000	0.015

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## TO-92 Suggested Pad Layout

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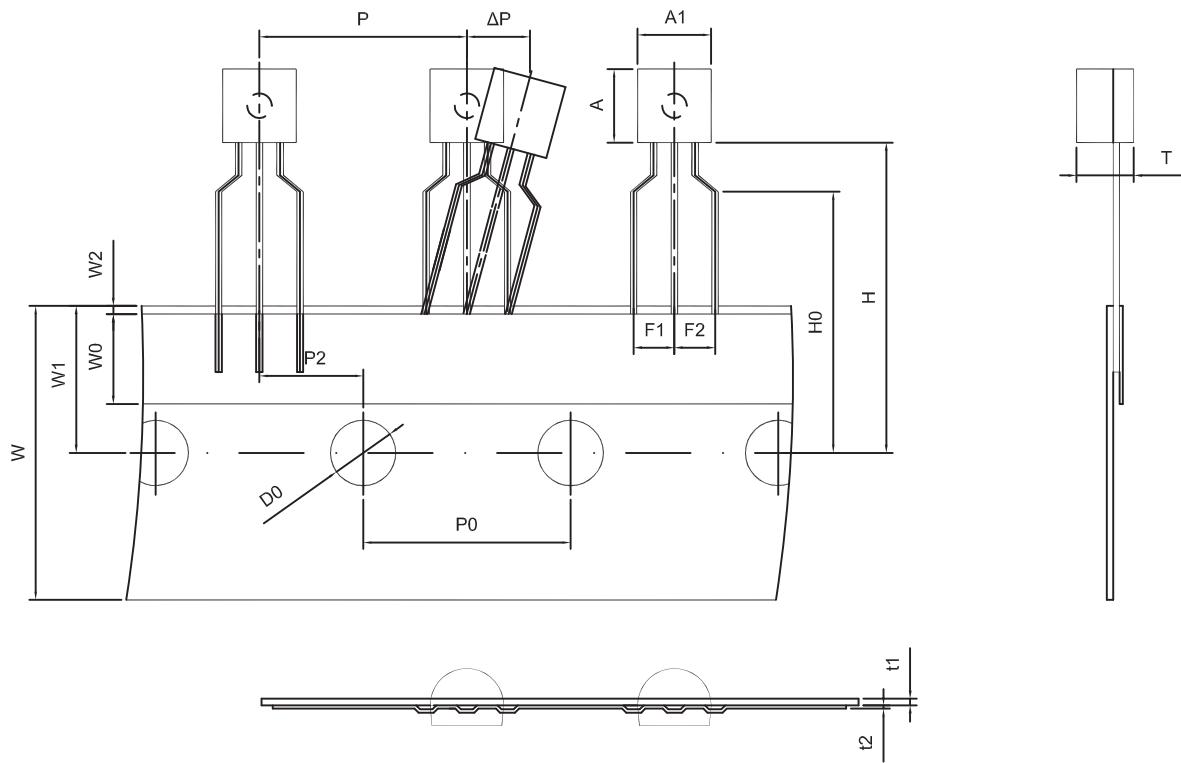


Note:

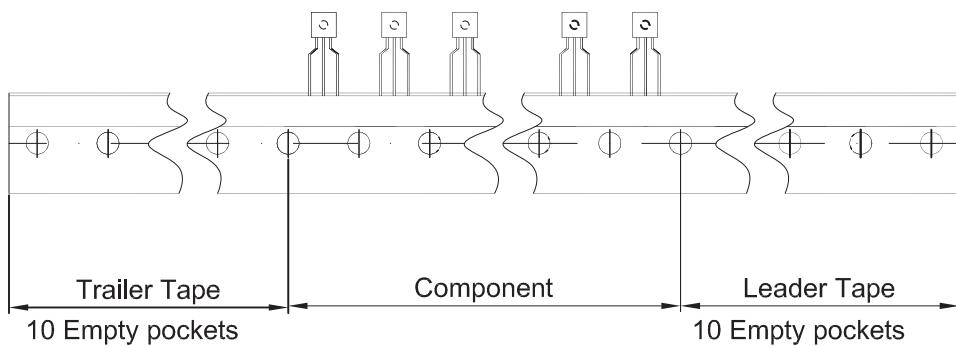
1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

## TO-92 Tape and Reel

### TO-92 PACKAGE TAPEING DIMENSION



Dimensions are in millimeter									
A1	A	T	P	P0	P2	F1	F2	W	
4.5±0.1	4.5±0.1	3.5±0.1	12.7±0.3	12.7±0.2	6.35±0.3	2.5±0.3	2.5±0.3	18.0+1.0/-0.5	
W0	W1	W2	H	H0	D0	t1	t2	ΔP	
6.0±0.5	9.0±0.5	1.0 MAX.	19.0±1.0	16.0±0.5	4.0±0.5	0.4±0.05	0.2±0.05	0 ± 1.0	



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250